

DATA SHEET

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74AHC2G00; 74AHCT2G00 2-input NAND gate

Product specification

2004 Jan 21

2-input NAND gate

74AHC2G00; 74AHCT2G00

FEATURES

- Symmetrical output impedance
- High noise immunity
- ESD protection:
 - HBM EIA/JESD22-A114-A exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
 - CDM EIA/JESD22-C101 exceeds 500 V.
- Low power dissipation
- Balanced propagation delays
- SOT505-2 and SOT765-1 package
- Specified from –40 to +85 °C and –40 to +125 °C.

DESCRIPTION

The 74AHC2G/AHCT2G00 is a high-speed Si-gate CMOS device.

The 74AHC2G/AHCT2G00 provides the 2-input NAND gate function.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25\text{ °C}$; $t_r = t_f \leq 3.0\text{ ns}$.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			AHC2G	AHCT2G	
t_{PHL}/t_{PLH}	propagation delay nA and nB to nY	$C_L = 15\text{ pF}$; $V_{CC} = 5\text{ V}$	3.5	3.6	ns
C_I	input capacitance		1.5	1.5	pF
C_{PD}	power dissipation capacitance per gate	$C_L = 50\text{ pF}$; $f = 1\text{ MHz}$; notes 1 and 2	17	18	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in Volts;
 N = total load switching outputs;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.
2. The condition is $V_I = \text{GND to } V_{CC}$.

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FUNCTION TABLE

See note 1.

INPUT		OUTPUT
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

Note

1. H = HIGH voltage level;
L = LOW voltage level.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE					
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING
74AHC2G00DP	-40 to +125 °C	8	TSSOP8	plastic	SOT505-2	A00
74AHCT2G00DP	-40 to +125 °C	8	TSSOP8	plastic	SOT505-2	C00
74AHC2G00DC	-40 to +125 °C	8	VSSOP8	plastic	SOT765-1	A00
74AHCT2G00DC	-40 to +125 °C	8	VSSOP8	plastic	SOT765-1	C00

PINNING

PIN	SYMBOL	DESCRIPTION
1	1A	data input
2	1B	data input
3	2Y	data output
4	GND	ground (0 V)
5	2A	data input
6	2B	data input
7	1Y	data output
8	V _{CC}	supply voltage

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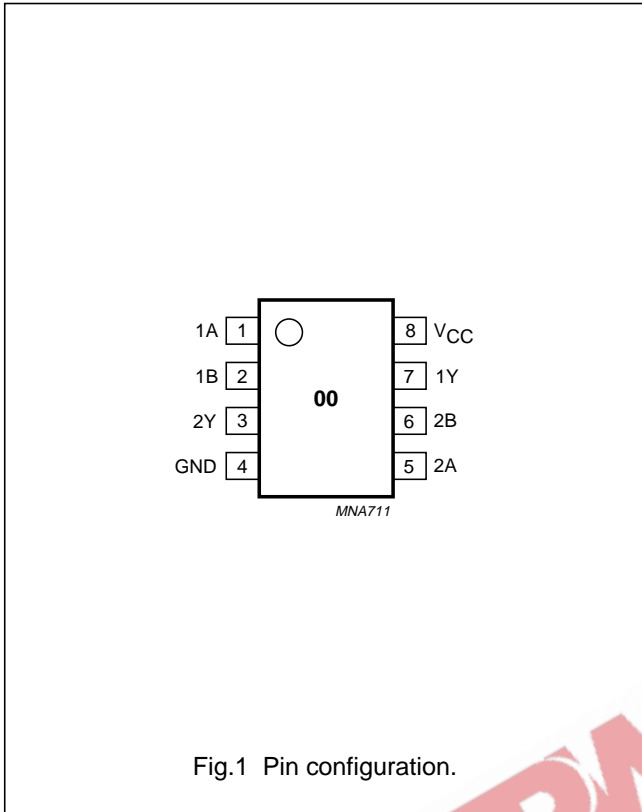


Fig.1 Pin configuration.

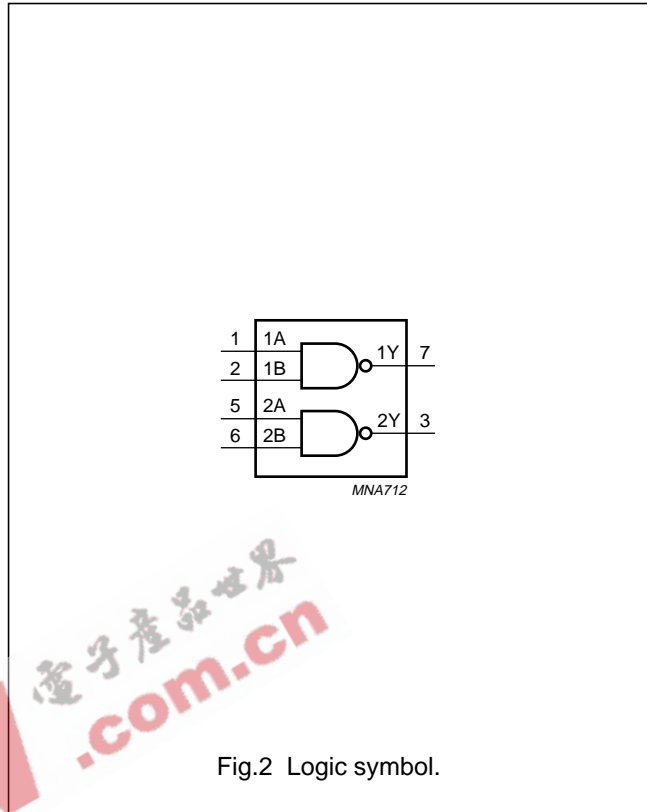


Fig.2 Logic symbol.

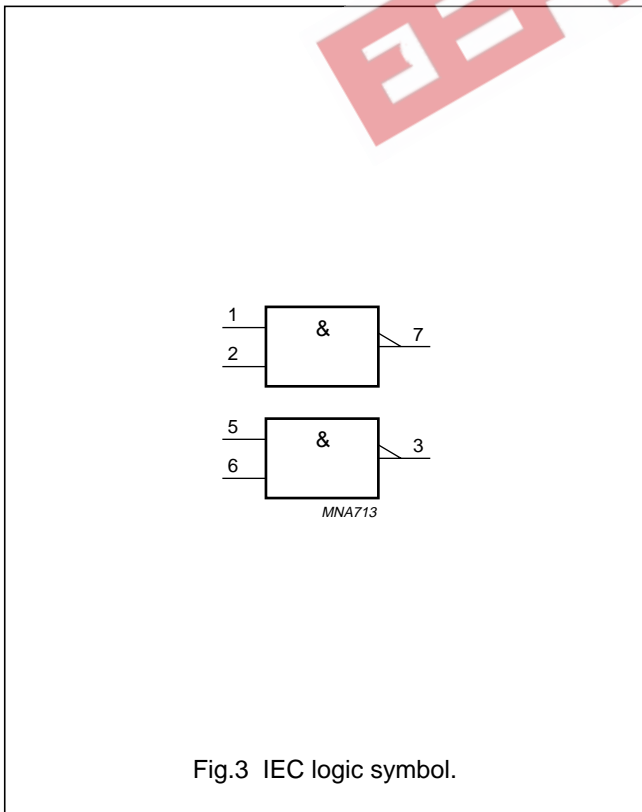


Fig.3 IEC logic symbol.

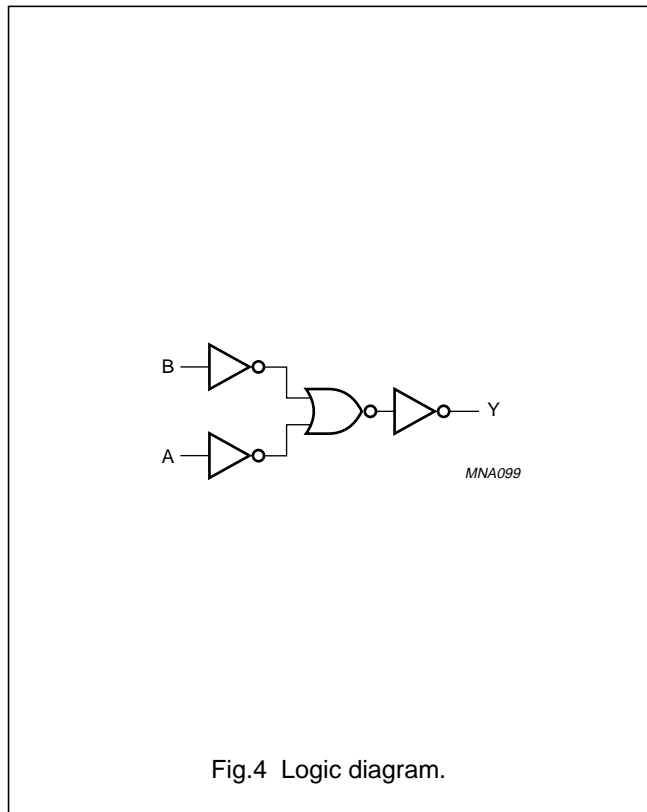


Fig.4 Logic diagram.

2-input NAND gate

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	74AHC2G00			74AHCT2G00			UNIT
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	–	5.5	0	–	5.5	V
V_O	output voltage		0	–	V_{CC}	0	–	V_{CC}	V
T_{amb}	operating ambient temperature	see DC and AC characteristics per device	–40	+25	+125	–40	+25	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 3.3 \pm 0.3$ V	–	–	100	–	–	–	ns/V
		$V_{CC} = 5 \pm 0.5$ V	–	–	20	–	–	20	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		–0.5	+7.0	V
V_I	input voltage		–0.5	+7.0	V
I_{IK}	input diode current	$V_I < -0.5$ V	–	–20	mA
I_{OK}	output diode current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V; note 1	–	±20	mA
I_O	output source or sink current	-0.5 V < V_O < $V_{CC} + 0.5$ V	–	±25	mA
I_{CC}, I_{GND}	V_{CC} or GND current		–	±75	mA
T_{stg}	storage temperature		–65	+150	°C
P_D	power dissipation	$T_{amb} = -40$ to $+125$ °C	–	250	mW

Note

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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DC CHARACTERISTICS

Type 74AHC2G00

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = 25 °C							
V _{IH}	HIGH-level input voltage		2.0	1.5	–	–	V
			3.0	2.1	–	–	V
			5.5	3.85	–	–	V
V _{IL}	LOW-level input voltage		2.0	–	–	0.5	V
			3.0	–	–	0.9	V
			5.5	–	–	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = –50 µA	2.0	1.9	2.0	–	V
		I _O = –50 µA	3.0	2.9	3.0	–	V
		I _O = –50 µA	4.5	4.4	4.5	–	V
		I _O = –4.0 mA	3.0	2.58	–	–	V
		I _O = –8.0 mA	4.5	3.94	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 µA	2.0	–	0	0.1	V
		I _O = 50 µA	3.0	–	0	0.1	V
		I _O = 50 µA	4.5	–	0	0.1	V
		I _O = 4.0 mA	3.0	–	–	0.36	V
		I _O = 8.0 mA	4.5	–	–	0.36	V
I _{LI}	input leakage current	V _I = V _{CC} or GND	5.5	–	–	0.1	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	10	µA
C _I	input capacitance		–	–	1.5	10	pF

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SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = -40 to +85 °C							
V _{IH}	HIGH-level input voltage		2.0	1.5	–	–	V
			3.0	2.1	–	–	V
			5.5	3.85	–	–	V
V _{IL}	LOW-level input voltage		2.0	–	–	0.5	V
			3.0	–	–	0.9	V
			5.5	–	–	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = -50 µA	2.0	1.9	–	–	V
		I _O = -50 µA	3.0	2.9	–	–	V
		I _O = -50 µA	4.5	4.4	–	–	V
		I _O = -4.0 mA	3.0	2.48	–	–	V
		I _O = -8.0 mA	4.5	3.8	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 µA	2.0	–	–	0.1	V
		I _O = 50 µA	3.0	–	–	0.1	V
		I _O = 50 µA	4.5	–	–	0.1	V
		I _O = 4.0 mA	3.0	–	–	0.44	V
		I _O = 8.0 mA	4.5	–	–	0.44	V
I _{LI}	input leakage current	V _I = V _{CC} or GND	5.5	–	–	1.0	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	10	µA
C _I	input capacitance		–	–	–	10	pF

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SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = -40 to +125 °C							
V _{IH}	HIGH-level input voltage		2.0	1.5	–	–	V
			3.0	2.1	–	–	V
			5.5	3.85	–	–	V
V _{IL}	LOW-level input voltage		2.0	–	–	0.5	V
			3.0	–	–	0.9	V
			5.5	–	–	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = -50 µA	2.0	1.9	–	–	V
		I _O = -50 µA	3.0	2.9	–	–	V
		I _O = -50 µA	4.5	4.4	–	–	V
		I _O = -4.0 mA	3.0	2.40	–	–	V
		I _O = -8.0 mA	4.5	3.70	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 µA	2.0	–	–	0.1	V
		I _O = 50 µA	3.0	–	–	0.1	V
		I _O = 50 µA	4.5	–	–	0.1	V
		I _O = 4.0 mA	3.0	–	–	0.55	V
		I _O = 8.0 mA	4.5	–	–	0.55	V
I _{LI}	input leakage current	V _I = V _{CC} or GND	5.5	–	–	2.0	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	40	µA
C _I	input capacitance		–	–	–	10	pF

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Type 74AHCT2G00

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = 25 °C							
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	–	–	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	–	–	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = –50 µA	4.5	4.4	4.5	–	V
		I _O = –8.0 mA	4.5	3.94	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 µA	4.5	–	0	0.1	V
		I _O = 8.0 mA	4.5	–	–	0.36	V
I _{LI}	input leakage current	V _I = V _{IH} or V _{IL}	5.5	–	–	0.1	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	1.0	µA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0	5.5	–	–	1.35	mA
C _I	input capacitance			–	1.5	10	pF
T_{amb} = –40 to +85 °C							
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	–	–	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	–	–	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = –50 µA	4.5	4.4	–	–	V
		I _O = –8.0 mA	4.5	3.8	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 50 µA	4.5	–	–	0.1	V
		I _O = 8.0 mA	4.5	–	–	0.44	V
I _{LI}	input leakage current	V _I = V _{IH} or V _{IL}	5.5	–	–	1.0	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	10	µA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0	5.5	–	–	1.5	mA
C _I	input capacitance		–	–	–	10	pF

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SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = -40 to +125 °C							
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	–	–	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	–	–	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}	4.5	4.4	–	–	V
		I _O = -50 μA I _O = -8.0 mA	4.5	3.70	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}	4.5	–	–	0.1	V
		I _O = 50 μA I _O = 8.0 mA	4.5	–	–	0.55	V
I _{LI}	input leakage current	V _I = V _{IH} or V _{IL}	5.5	–	–	2.0	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	40	μA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0	5.5	–	–	1.5	mA
C _I	input capacitance		–	–	–	10	pF

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AC CHARACTERISTICS

Type 74AHC2G00

GND = 0 V; $t_r = t_f \leq 3.0$ ns.

SYMBOL	PARAMETER	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	C _L (pF)	V _{CC} (V)				
T_{amb} = 25 °C								
t _{PHL} /t _{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	3.0 to 3.6	–	4.5 ⁽¹⁾	7.9	ns
				4.5 to 5.5	–	3.5 ⁽²⁾	5.5	ns
		50	3.0 to 3.6	–	6.5 ⁽¹⁾	11.4	ns	
			4.5 to 5.5	–	4.9 ⁽²⁾	7.5	ns	
T_{amb} = –40 to +85 °C								
t _{PHL} /t _{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	3.0 to 3.6	1.0	–	9.5	ns
				4.5 to 5.5	1.0	–	6.5	ns
		50	3.0 to 3.6	1.0	–	13.0	ns	
			4.5 to 5.5	1.0	–	8.5	ns	
T_{amb} = –40 to +125 °C								
t _{PHL} /t _{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	3.0 to 3.6	1.0	–	10.5	ns
				4.5 to 5.5	1.0	–	7.0	ns
		50	3.0 to 3.6	1.0	–	14.5	ns	
			4.5 to 5.5	1.0	–	9.5	ns	

Notes

1. Typical values are measured at V_{CC} = 3.3 V.
2. Typical values are measured at V_{CC} = 5.0 V.

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Type 74AHCT2G00GND = 0 V; $t_r = t_f \leq 3.0$ ns.

SYMBOL	PARAMETER	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	C_L (pF)	V_{CC} (V)				
$T_{amb} = 25\text{ }^\circ\text{C}$								
t_{PHL}/t_{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	4.5 to 5.5	1.0	3.6 ⁽¹⁾	6.2	ns
			50	4.5 to 5.5	1.0	5.0 ⁽¹⁾	7.9	ns
$T_{amb} = -40\text{ to }+85\text{ }^\circ\text{C}$								
t_{PHL}/t_{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	4.5 to 5.5	1.0	–	7.1	ns
			50	4.5 to 5.5	1.0	–	9.0	ns
$T_{amb} = -40\text{ to }+125\text{ }^\circ\text{C}$								
t_{PHL}/t_{PLH}	propagation delay input nA and nB to output nY	see Figs 5 and 6	15	4.5 to 5.5	1.0	–	8.0	ns
			50	4.5 to 5.5	1.0	–	10.0	ns

Note

- Typical values are measured at $V_{CC} = 5.0$ V.

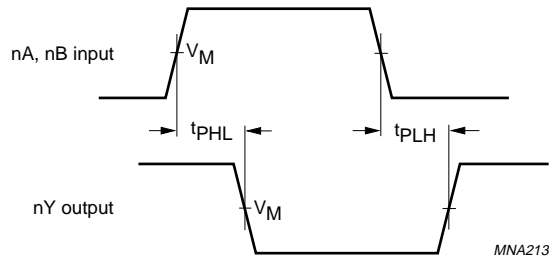


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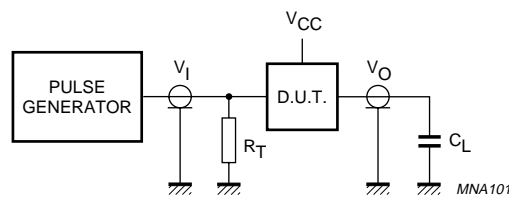
74AHC2G00; 74AHCT2G00

AC WAVEFORMS



FAMILY	V _M INPUT	V _M OUTPUT
AHC2G00	50% V _{CC}	50% V _{CC}
AHCT2G00	1.5 V	50% V _{CC}

Fig.5 The inputs (nA and nB) to output (nY) propagation delays.



FAMILY	V _I INPUT REQUIREMENTS
AHC2G00	GND to V _{CC}
AHCT2G00	GND to 3.0 V

Definitions for test circuit:

C_L = Load capacitance including jig and probe capacitance (See "AC characteristics" for the value).

R_T = Termination resistance should be equal to the output impedance Z₀ of the pulse generator.

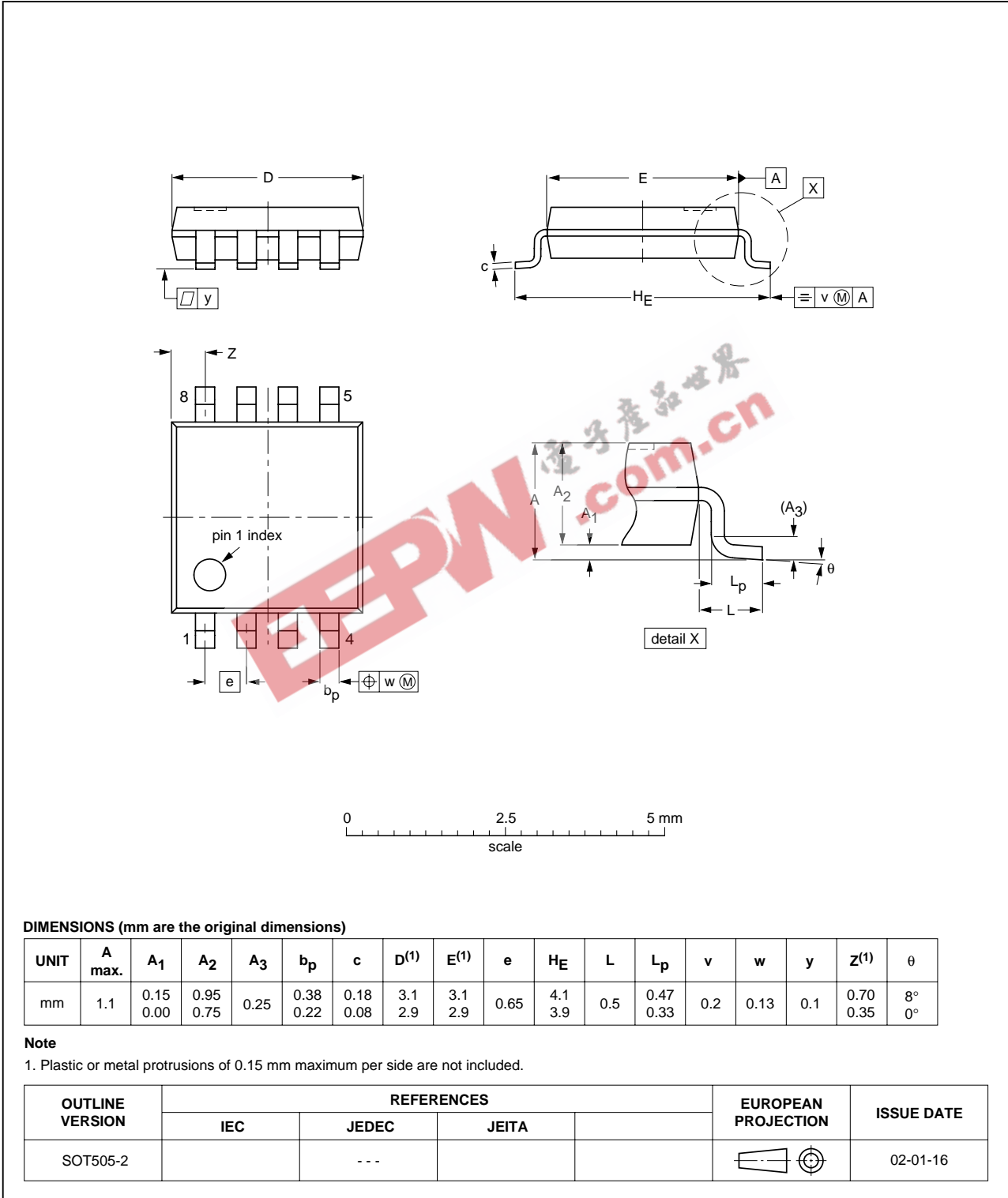
Fig.6 Load circuitry for switching times.

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PACKAGE OUTLINES

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

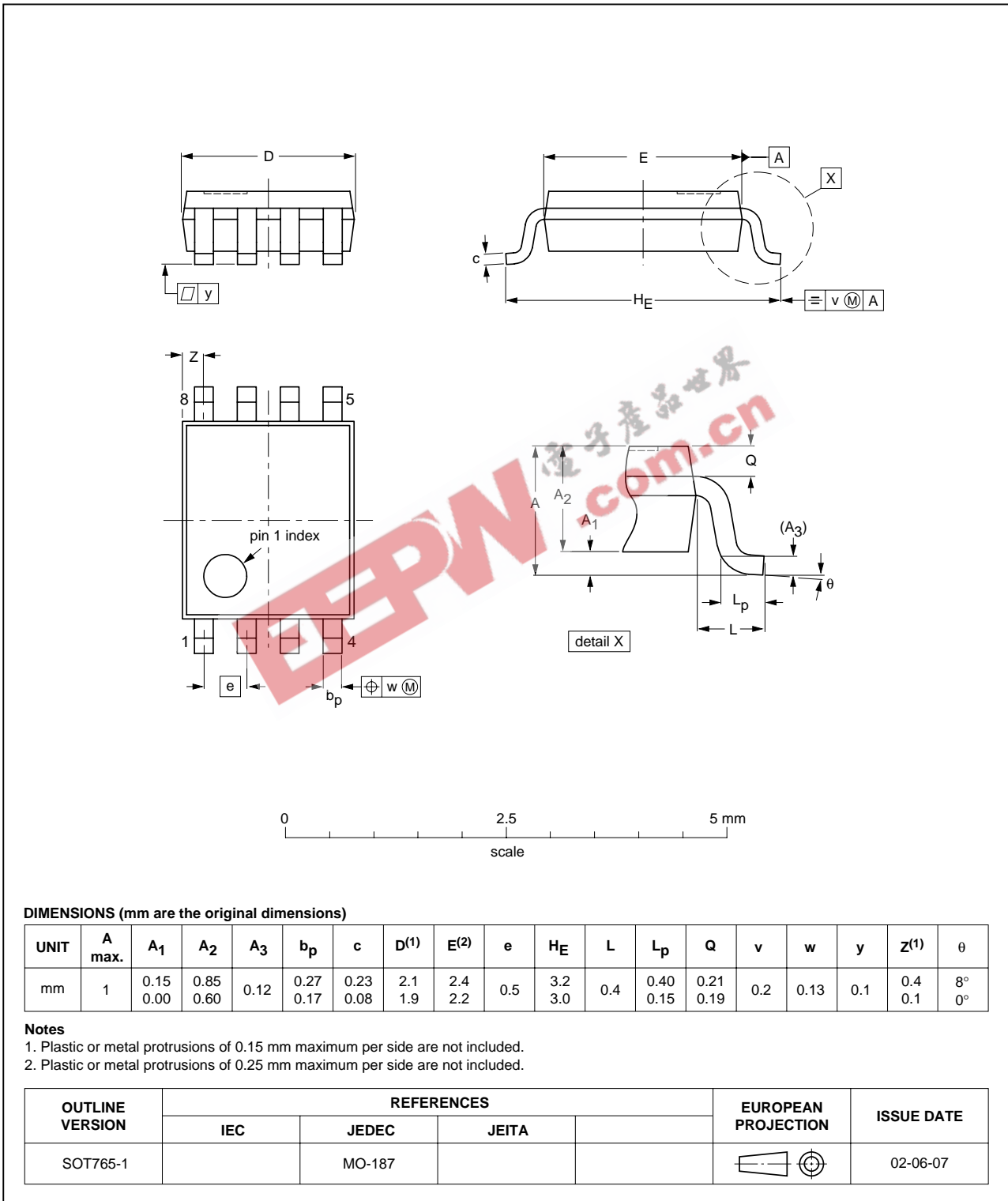


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VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



2-input NAND gate

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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